

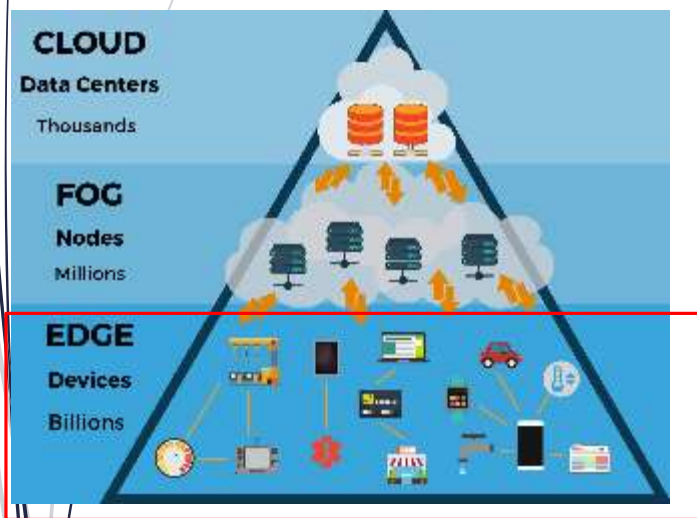


# chist-era

UNICO - Unsupervised spiking neural networks with analog memristive devices for edge computing

2

## UNICO: Spiking Neural network for Edge Computing Applications



Signals with strong temporal signature from sensors

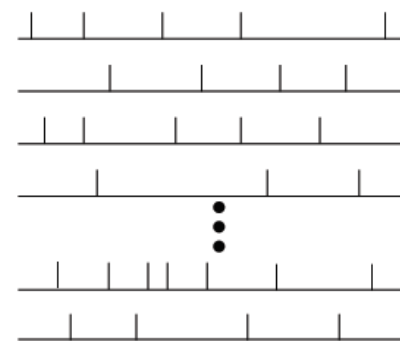
ToF camera



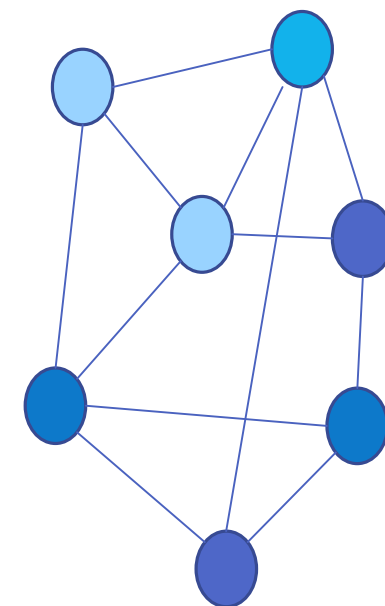
Bio-signals (e.g. EMG)



Spike encoding



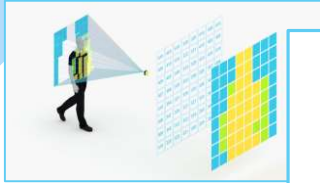
Spike computing



3

Signals from sensors

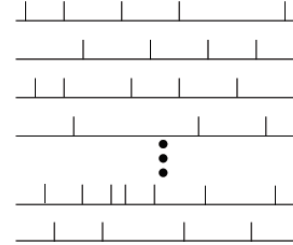
ToF camera



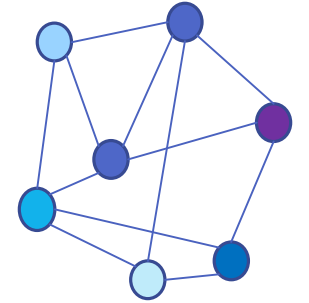
Bio-signals (e.g. EMG)



Spike encoding



Spike computing



## Key challenges and opportunities

SOFTWARE

- Identification of spatio-temporal features
- In-sensor computing
- Footprints/Energy constraints (Edge Computing)

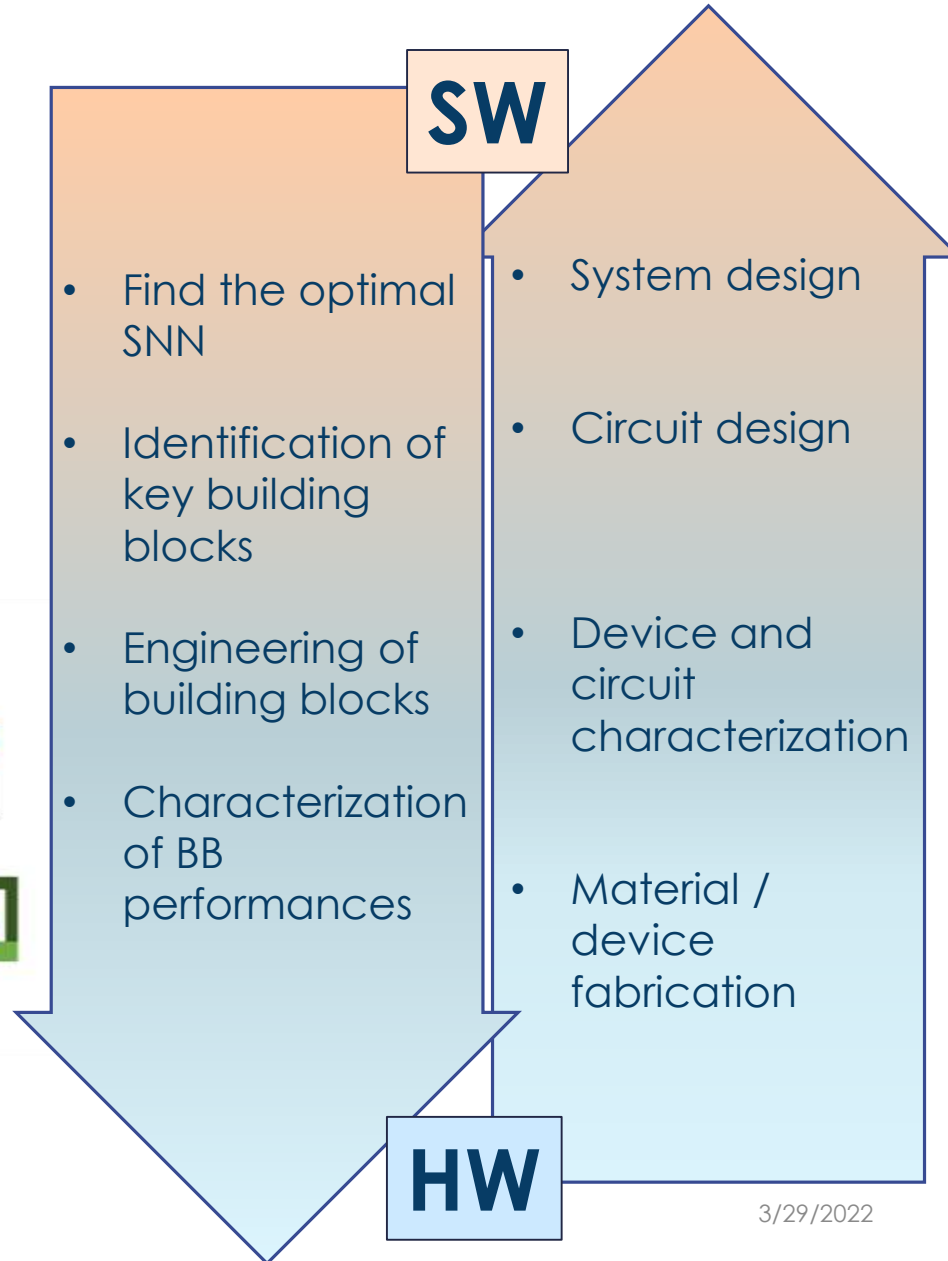
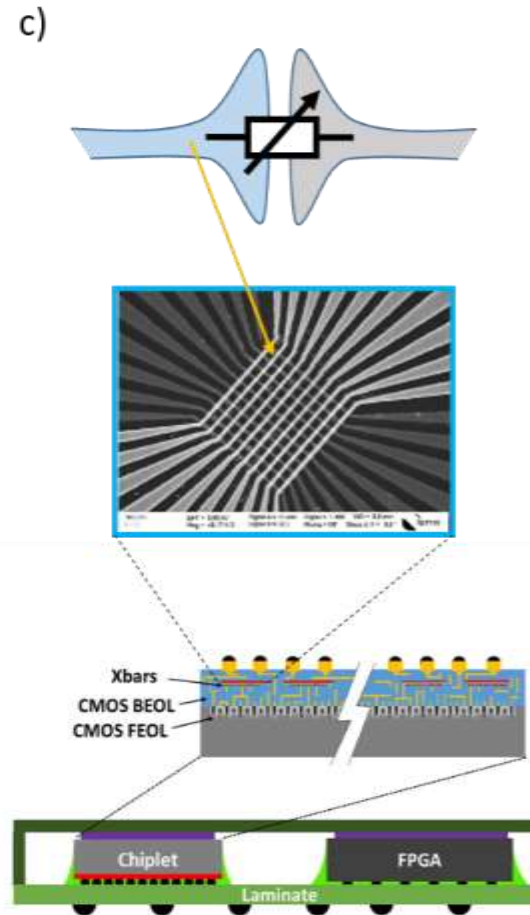
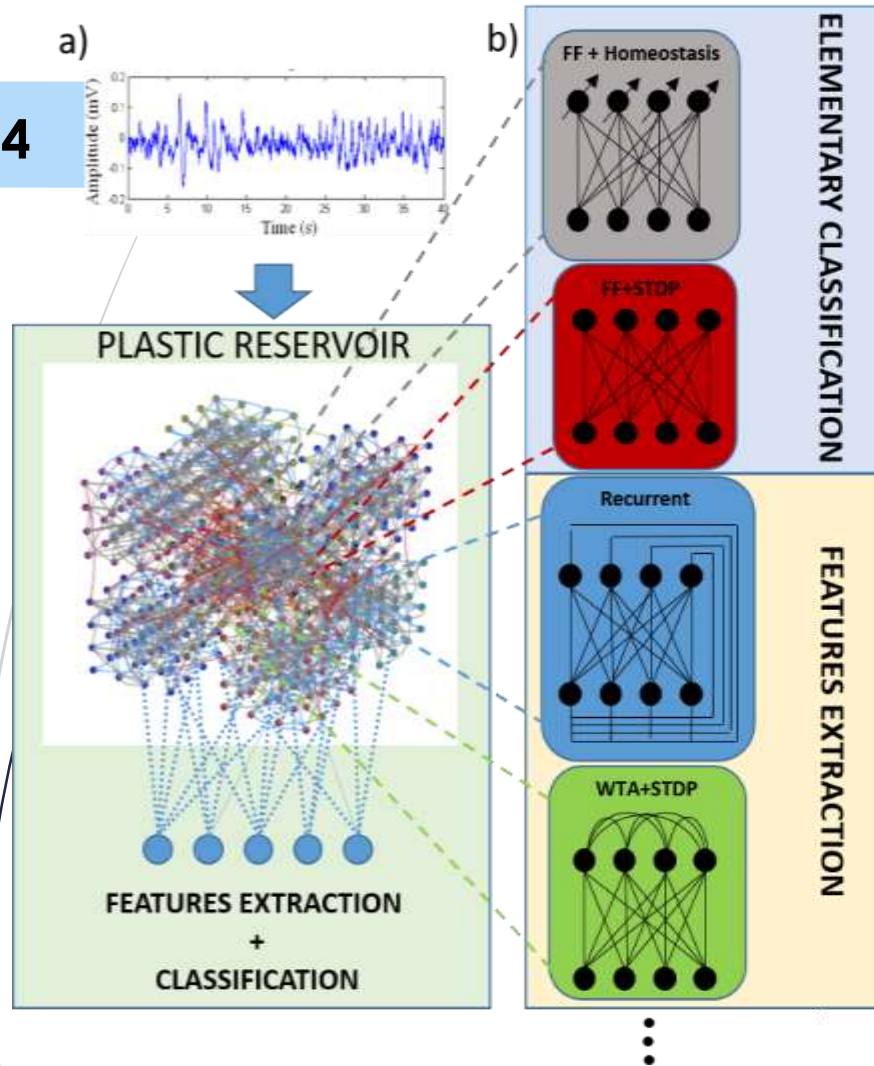
- Features enhancement vs full band encoding
- Event sensor vs continuous analog signals (time and frequency)
- Circuit design for encoding

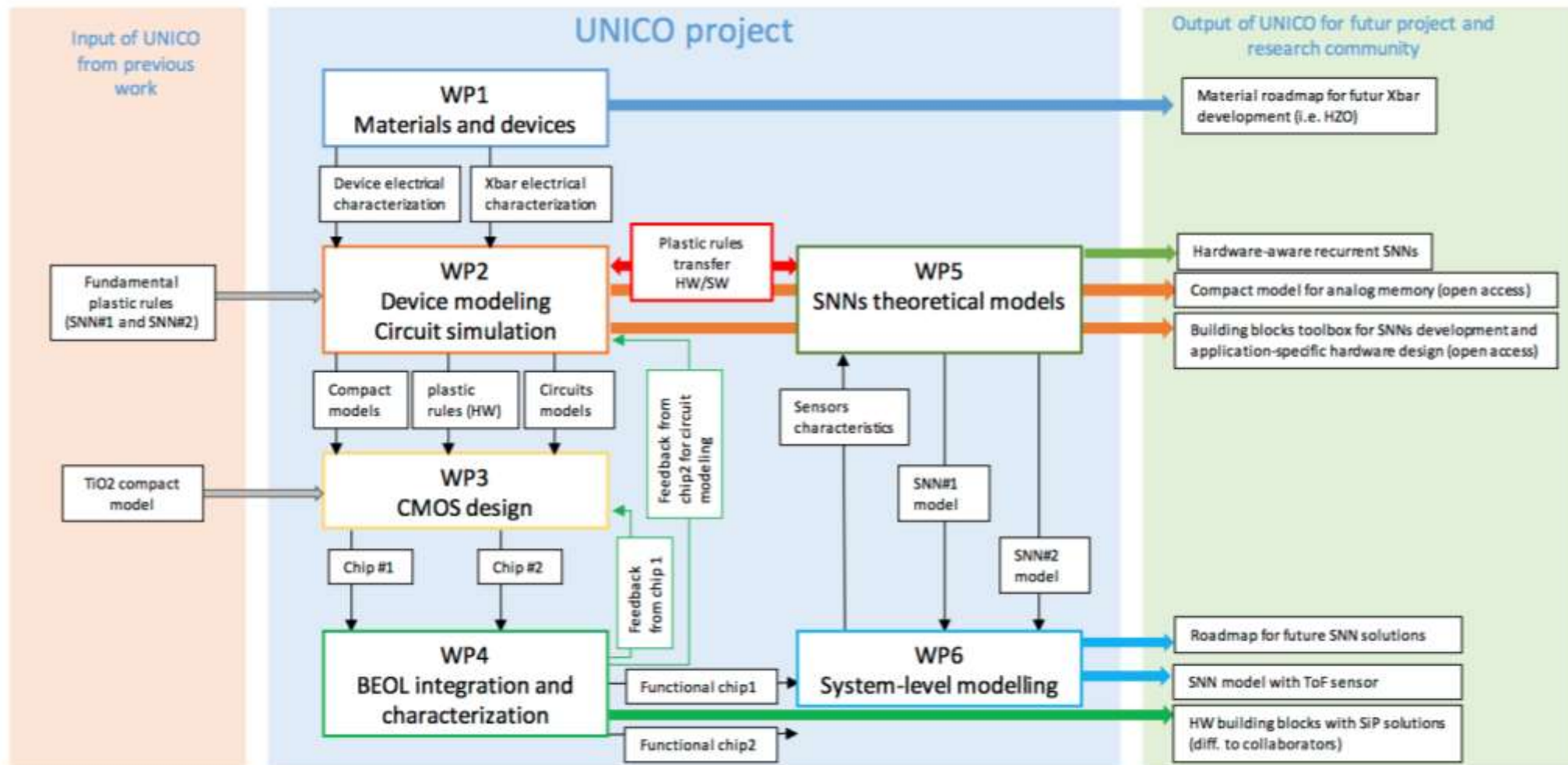
- Benchmarking / performances
- SNN definition
- Hardware mapping opportunities and constraints

HARDWARE

# The software/hardware strategy

4





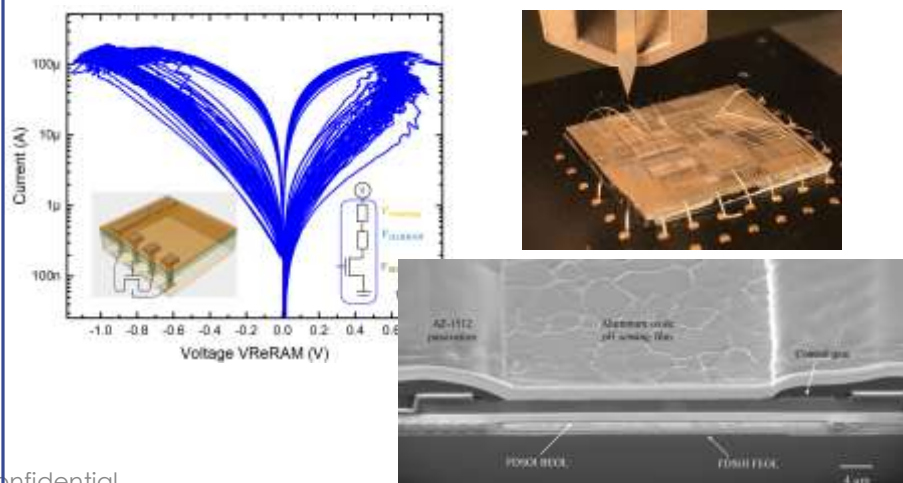
# Involvement

6

- ▶ Université de Sherbrooke (CA, UdeS-Nano & UdeS-ML) Coordinator
- ▶ CNRS / C2N (FR)
- ▶ CNRS/ Aix-Marseille University (FR)
- ▶ IBM-Zurich (CH)
- ▶ Jagiellonian University with CEZAMAT PW (PL)

## NANOELECTRONIC GROUP (Pr. D. Drouin)

The NANOELECTRONIC group has strong expertise in nanodevices fabrication, BEOL integration and packaging. The group evolves in a academic / industry transfer oriented environment (C2MI, IBM-Bromont).

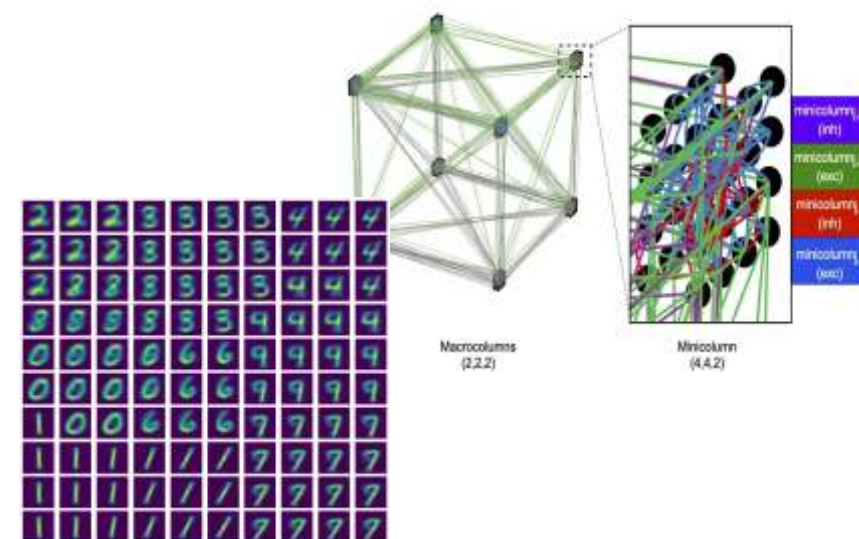


## NECOTIS GROUP

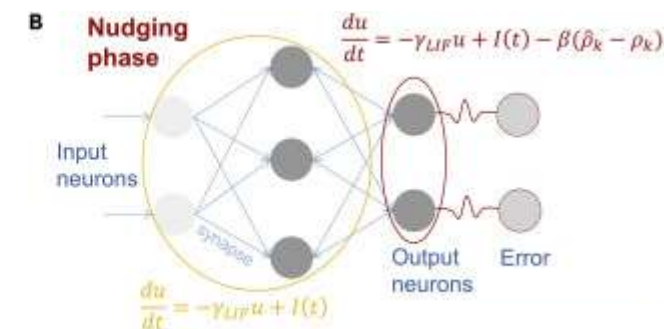
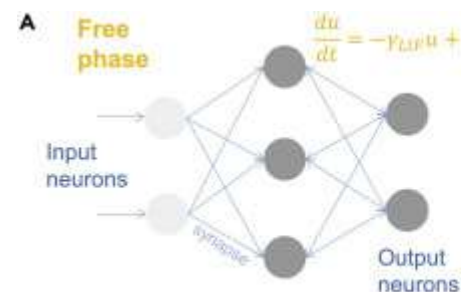
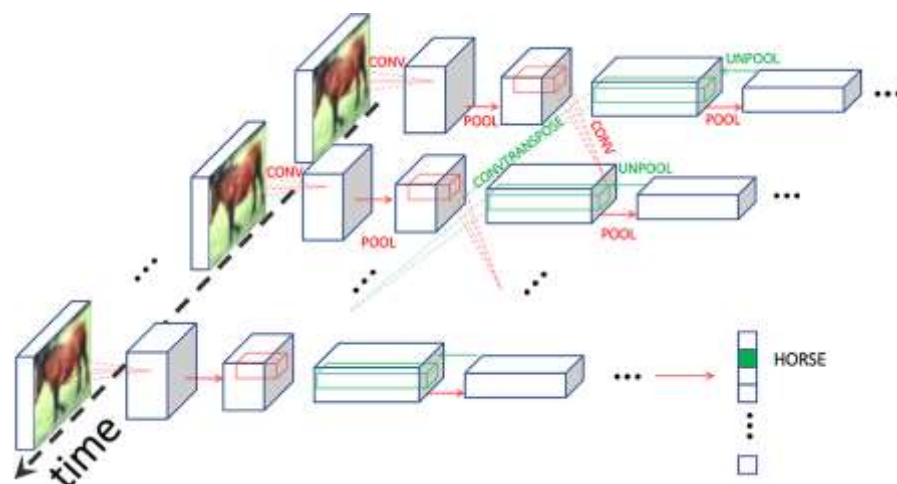
(Neurosciences computationnelles et traitement intelligent des signaux)

(Pr. J. Rouat)

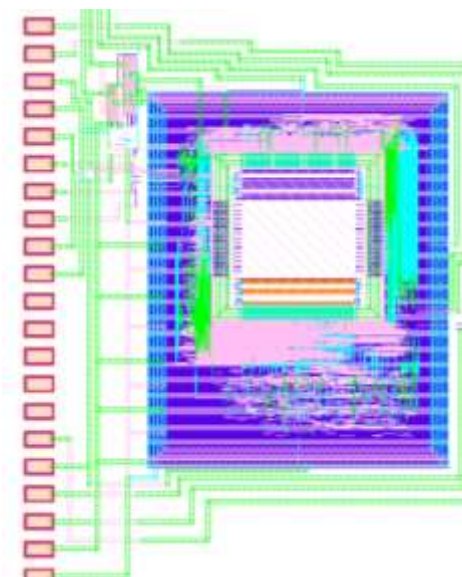
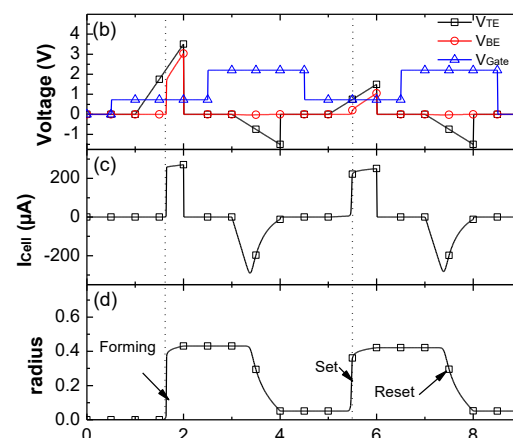
NECOTIS is a pioneering group in neuromorphic computing with interest in data analysis, spike computing and exploration of new SNN topologies



- Université Paris-Saclay (Centre de Nanosciences et de Nanotechnologies / C2N)
- Expert on the development of neural networks specific to neuromorphic/memristive hardware
- Provided assistance for the development of VDSP
- Currently developing an approach inspired by « Equilibrium Propagation » to scale VDSP to deep neural networks
  - *Large-scale simulations and planned small-scale validation on the UNICO demonstrator*

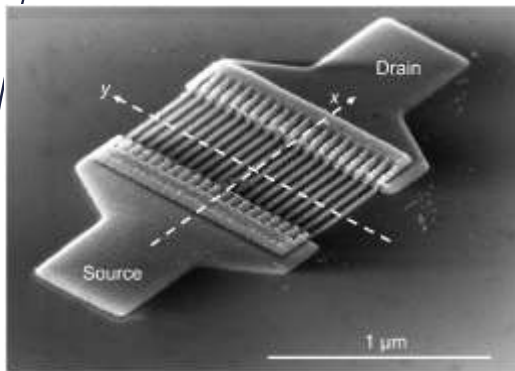
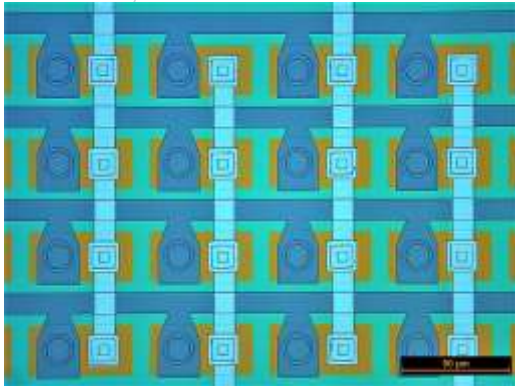


AMU (IM2NP): The memories team at AMU (IM2NP) works exclusively on non-volatile memory technologies, covering several aspects from material science (e.g. AFM analysis), device electrical characterization, memory cell analytical and compact modeling, and memory circuit design with emphasis on IMC concept for AI applications.



# IBM Research | Zurich

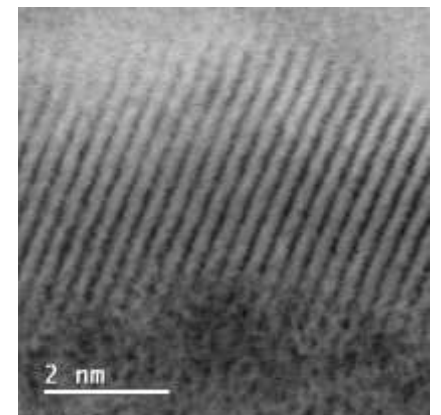
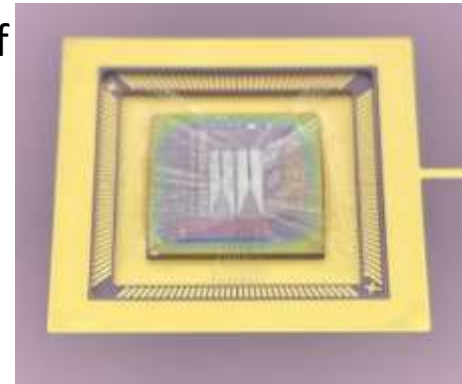
10

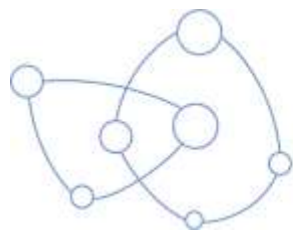


Established in 1956 in Switzerland, it represents the European branch of IBM Research (~300 employees)

**Infrastructure:** state-of-the-art cleanroom facilities (Binnig and Rohrer Nanotechnology Center) for processing nano-scale devices, advanced thin-film deposition techniques, materials characterization equipment. Characterization facilities for investigating memristive components and circuits.

**Exploitation strategy** (in addition to dissemination): Enabling technology for AI hardware: potential technology transfer to IBM's Albany Nanotechnology Center.





**CEZAMAT**  
POLITECHNIKA WARSZAWSKA

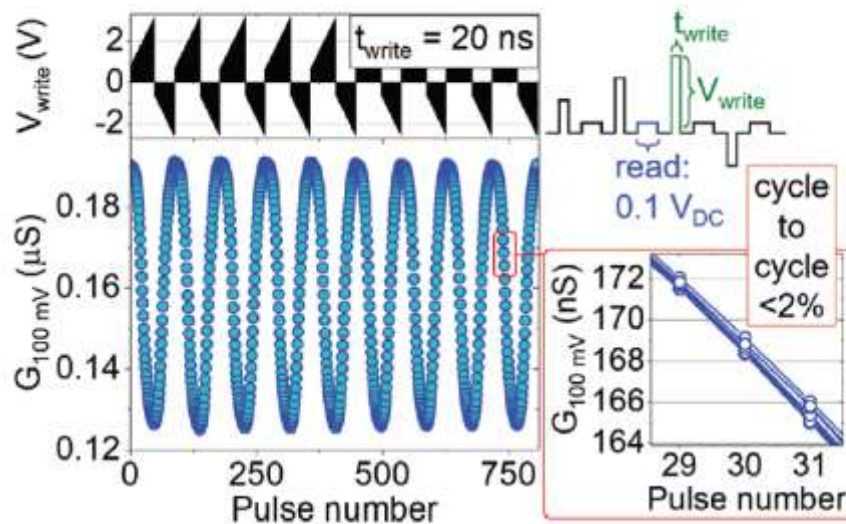
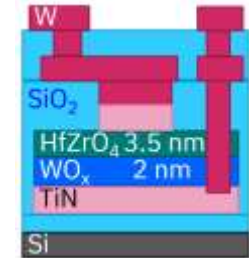


JAGIELLONIAN UNIVERSITY  
IN KRAKÓW

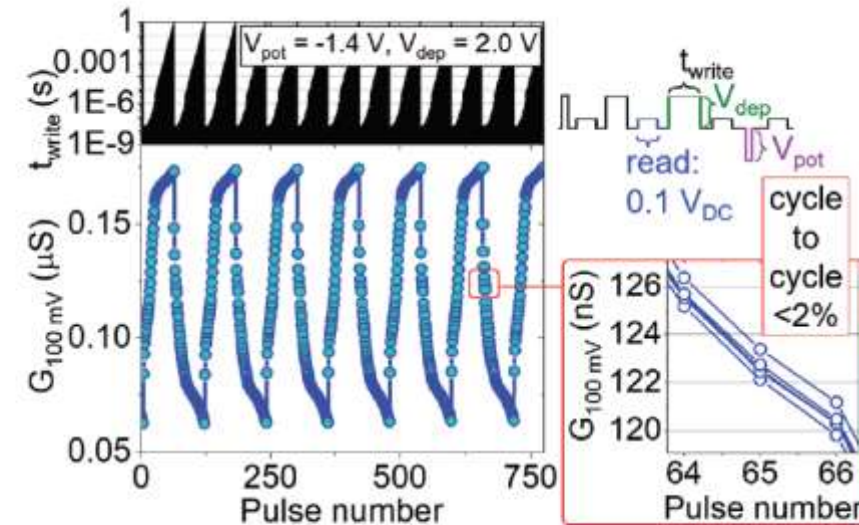
CEZAMAT partner is leading the ToF sensor technology. They have strong expertise in ToF technology, design of Front End/Back End of sensors. They are developing the software environment for the UNICO project.



$\text{HfZrO}_4$  deposited by Atomic Layer Deposition then crystallised in the ferroelectric phase at  $400^\circ\text{C}$   
 Remanent electrical polarisation: **Ferroelectric Field-Effects** in 2 or 3 terminals configuration.  
**Analog resistive switching** obtained by the gradual switching of ferroelectric domains.



**Figure 4.** Synaptic potentiation and depression with pulses of increasing amplitude. The pulse amplitude  $V_{\text{write}}$  and the pulse duration  $t_{\text{write}}$  are defined as in the measurement scheme (top right). The inset shows the cycle-to-cycle variation.

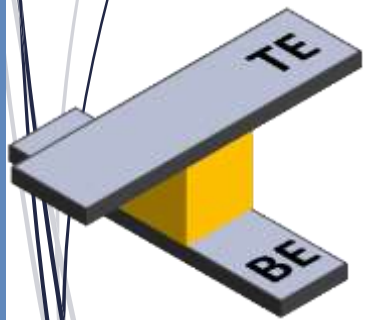
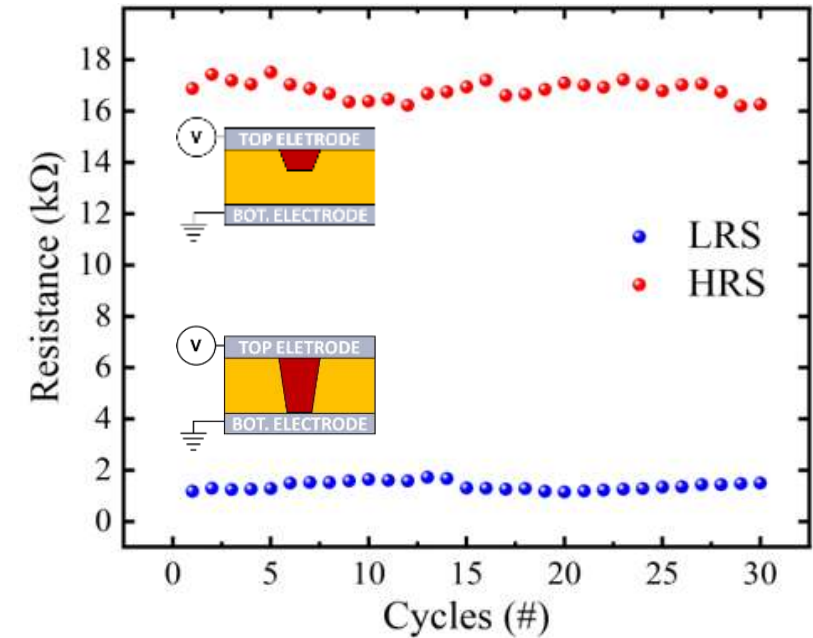
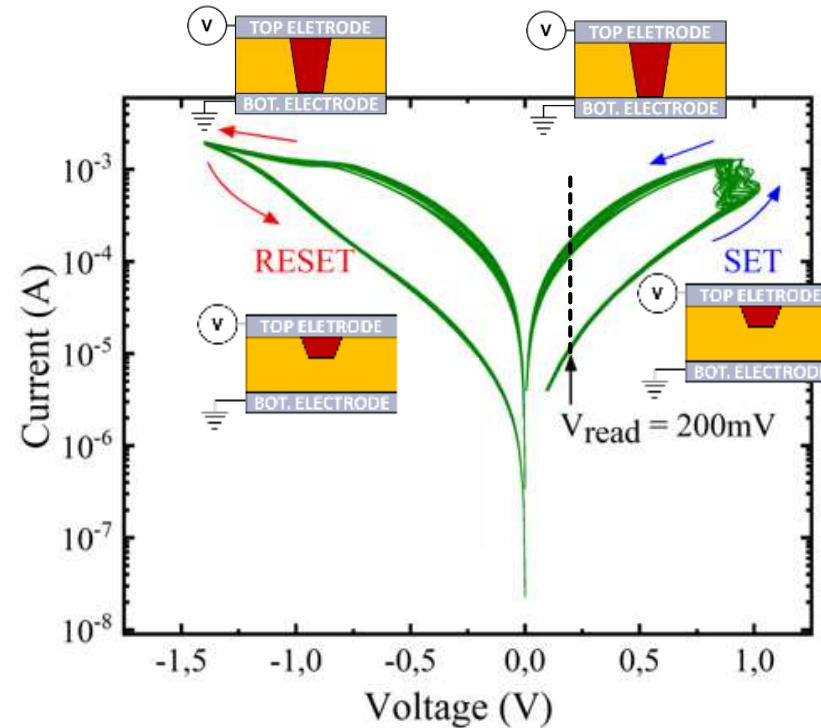
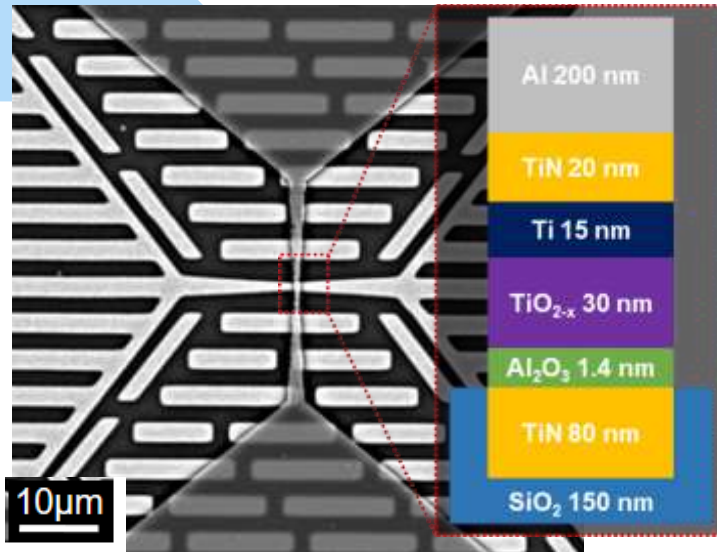


**Figure 5.** Long-term potentiation and depression for pulses with constant amplitudes  $V_{\text{pot}}$  and  $V_{\text{dep}}$  (as defined in the measurement scheme) and increasing duration  $t_{\text{width}}$ . The inset shows the cycle-to-cycle variation.

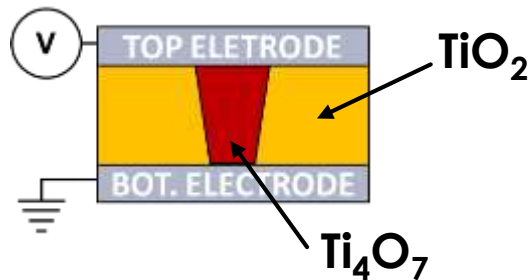
Bégon-Lours *et al.* Adv. Elec. Mat. (2022)  
<https://doi.org/10.1002/aelm.202101395>.

# Material/devices: TiOx optimization

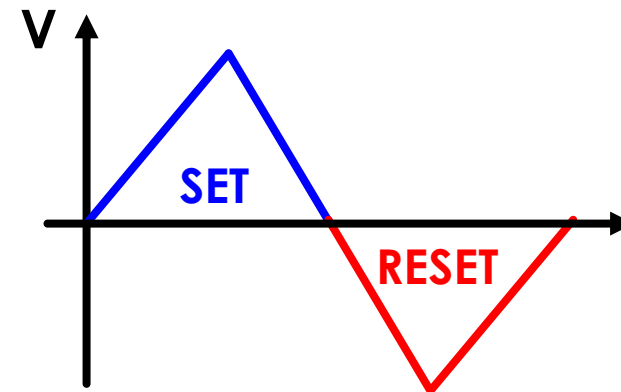
Top SEM view



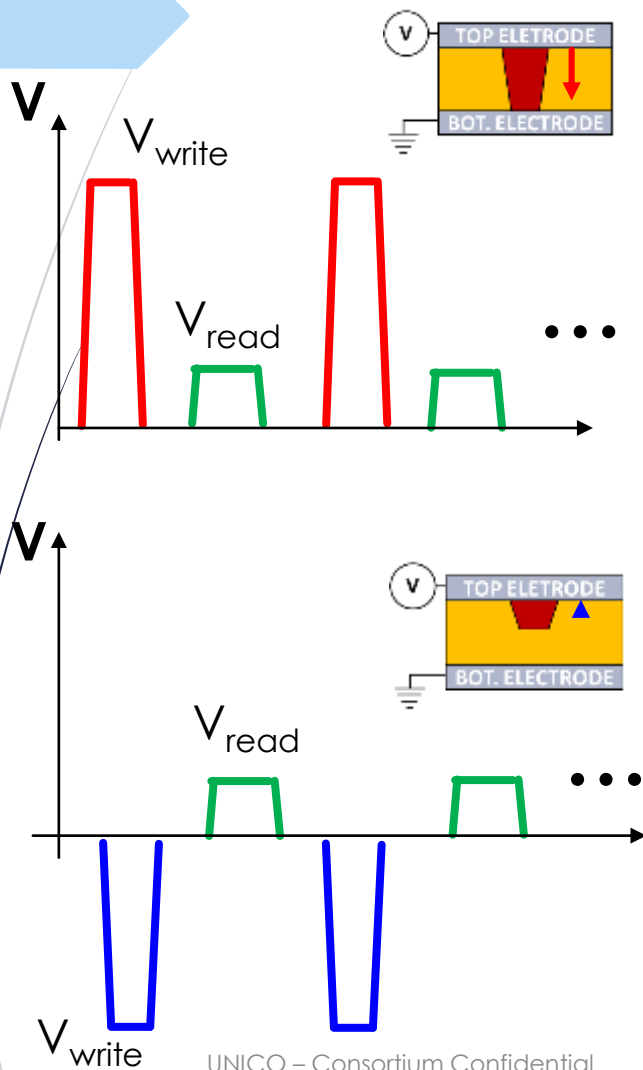
3D view



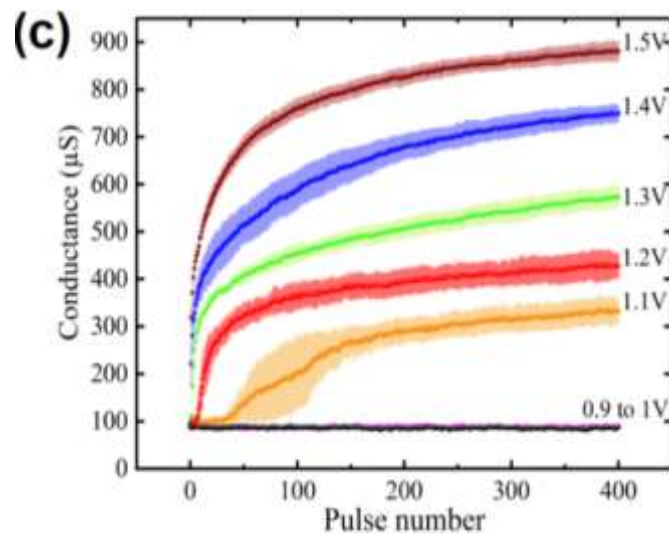
Side view



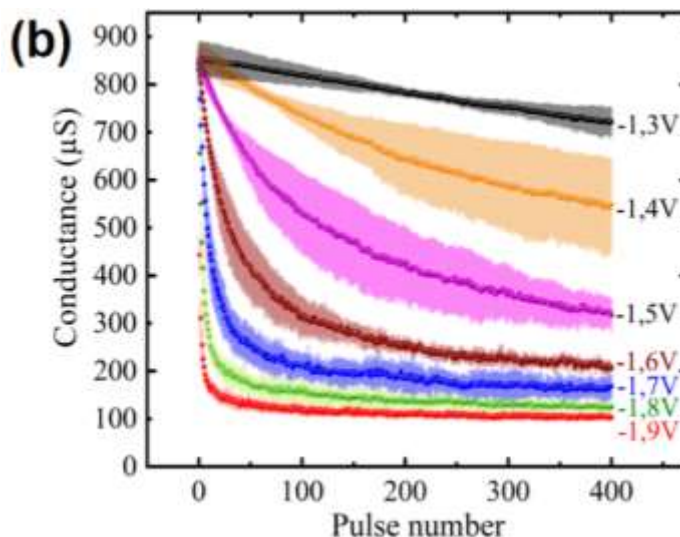
# Material/devices: TiOx optimization



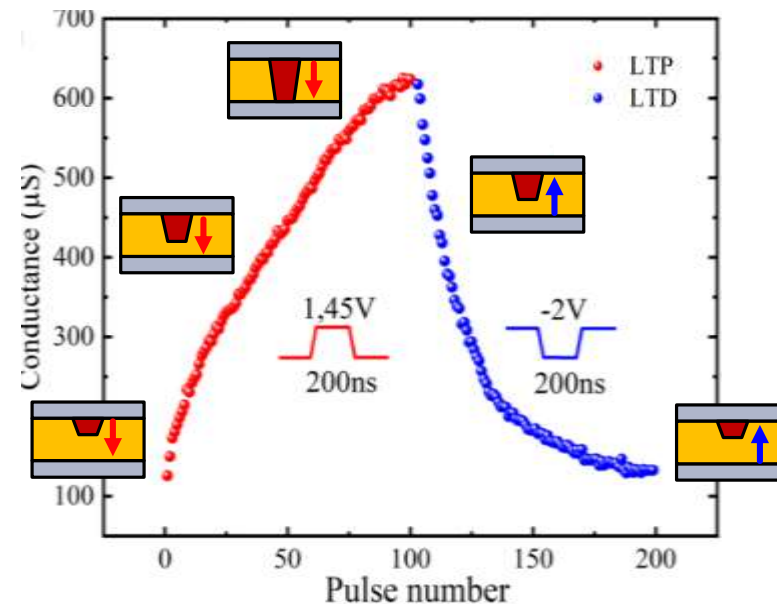
Long-term potentiation (LTP)



Long-term depression (LTD)



LTP followed by LTD: Synaptic plasticity



Conductance-to-weight:

$$W = \frac{g - g_{min}}{g_{max} - g_{min}}$$

# Devices: benchmarking

15

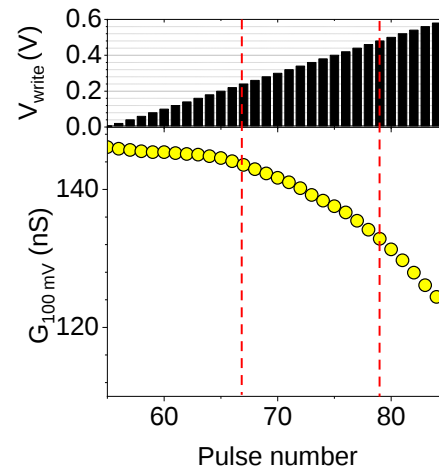
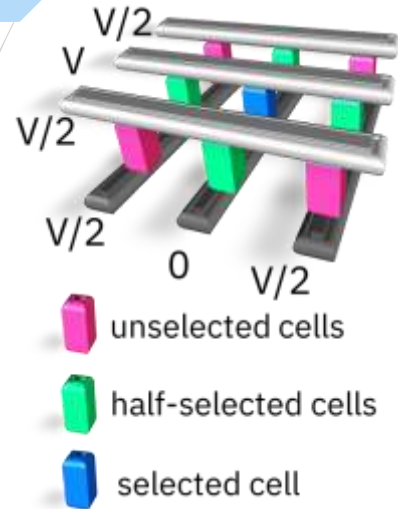
Comparison of key metrics of the devices developped in UNICO

|               | RTO FeFET                                        | ALD FeFET                   | FinFeFET                         | FTJ 5 nm                       | FTJ 4 nm                                  | FTJ 3 nm                                         | IBM TiOx             | 3IT TiOx             | RRAM MOx             |
|---------------|--------------------------------------------------|-----------------------------|----------------------------------|--------------------------------|-------------------------------------------|--------------------------------------------------|----------------------|----------------------|----------------------|
|               | <i>Halter ACS Appl. Mater. Interfaces (2020)</i> | <i>Halter, under review</i> | <i>Falcone, Frontiers (2022)</i> | <i>Bégon-Lours JEDS (2021)</i> | <i>Bégon-Lours Adv. Elec. Mat. (2022)</i> | <i>Bégon-Lours Neur. Comp. &amp; Eng. (2022)</i> |                      |                      |                      |
| Dynamic Range | 1.9                                              | <b>10 to 60</b>             | 1.4                              | 7.2                            | 7                                         | 1.3                                              | 2 to 10              | 2 to 20              | 3                    |
| Ron           | >100 kOhms                                       | 10 Mohms to 500 Mohms       | 1 MOhms                          | 1 GOhms                        | 10 MOhms                                  | 10 MOhms                                         | 100 Ohms             | 1 kOhms              | 1-100 kOhms          |
| N states      | 20                                               | >100                        | >100                             | >100                           | >100                                      | >100                                             | 10                   | >100                 | 20                   |
| Prog time     | 50 ns to 5 us                                    | 10 ns to 1 s                | 50 ns to 5 us                    | 10 ns to 1 s                   | 10 ns to 1 s                              | 10 ns to 1 s                                     | 800 ns               | ~100 ns              | 200 ns to 1 us       |
| Prog Voltage  | 3 V                                              | 6 V                         | 5 V                              | 3 V                            | 2 V                                       | <b>1 V</b>                                       | 1.2 V                | 1.5 V                | 2 V                  |
| Write energy  | 0.5 fJ                                           | 1.2 pJ                      | 1 fJ                             | 1 pJ                           | 1 pJ                                      | 1 pJ                                             | 1 nJ                 | 10-100 pJ            | 200 pJ               |
| Area          | 2E1 um <sup>2</sup>                              | 1E-1 um <sup>2</sup>        | <b>1E-3 um<sup>2</sup></b>       | 1E4 um <sup>2</sup>            | 1E2 um <sup>2</sup>                       | 1E1 um <sup>2</sup>                              | 1E-2 um <sup>2</sup> | 1E-2 um <sup>2</sup> | 1E-3 um <sup>2</sup> |
| D-to-D        | 100%                                             | 38%                         | 50%                              | <2%                            | <2%                                       | <2%                                              |                      |                      | 20%                  |
| C-to-C        | 1%                                               | 1.90%                       | 5.00%                            | <2%                            | <2%                                       | <2%                                              | 10%                  |                      | 5%                   |
| Endurance     | 8,00E+06                                         | >1e10                       | NC                               | >1e10                          | >1e10                                     | >1e10                                            |                      |                      | >1e6                 |

# Circuit: HZO passive crossbar integration

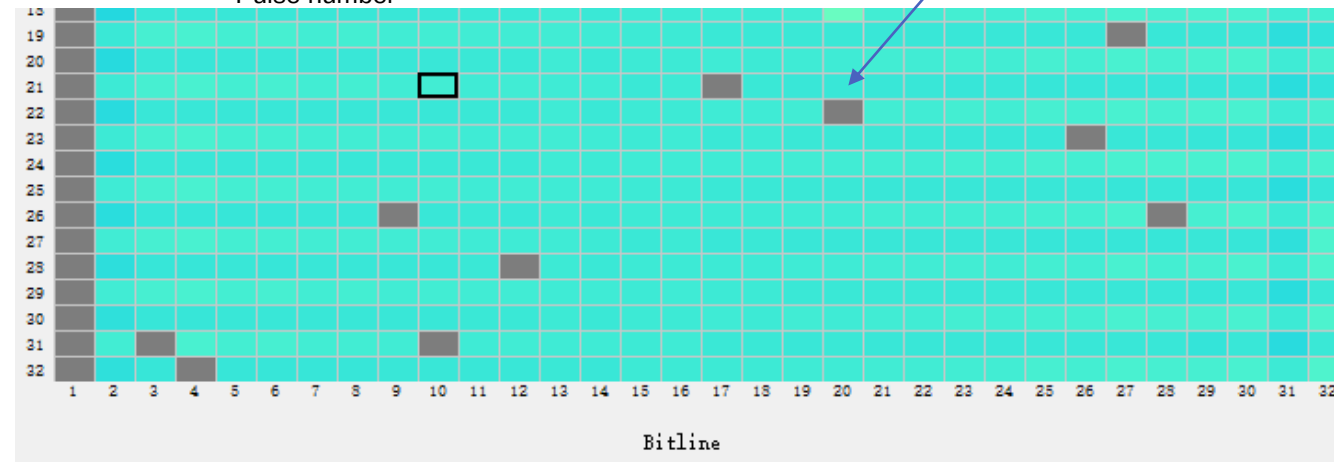
16

## T1.3: Integration of HZO into crossbar arrays:



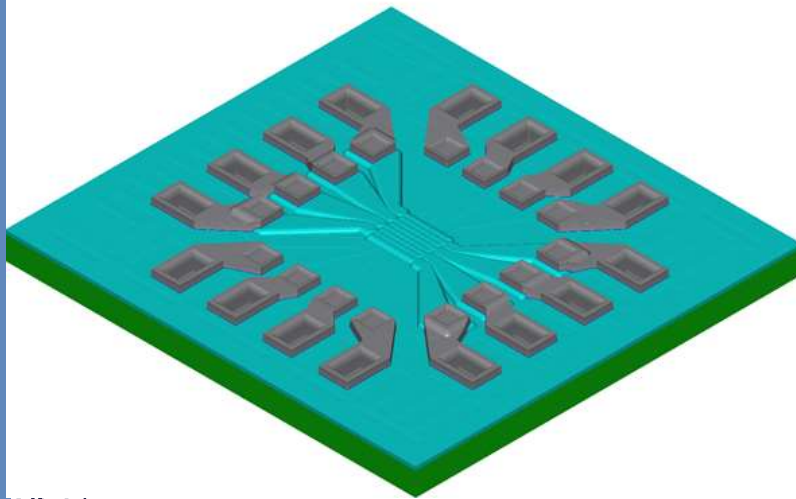
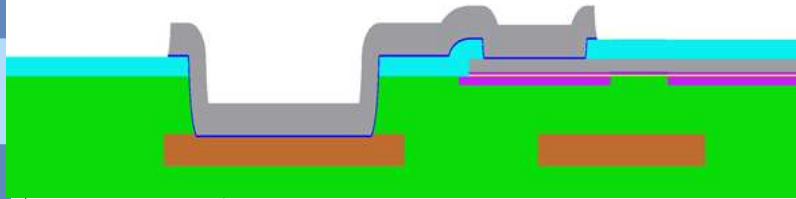
Half-selection scheme reduces the available dynamic range: half-selected cells can be disturbed if  $V_{write}/2$  higher than  $E_C$

Array with access pads to disconnect shorted devices at M2

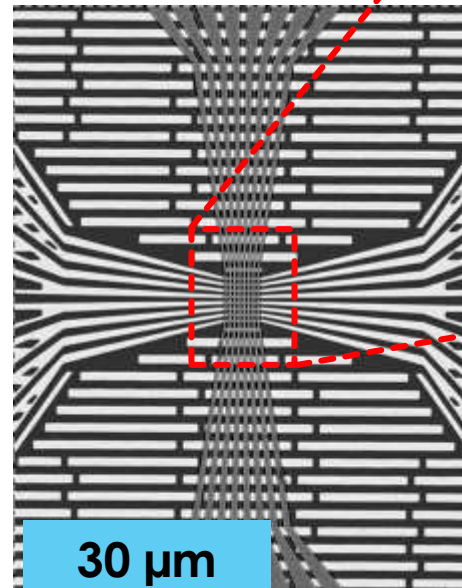


# Circuit: BEOL integration

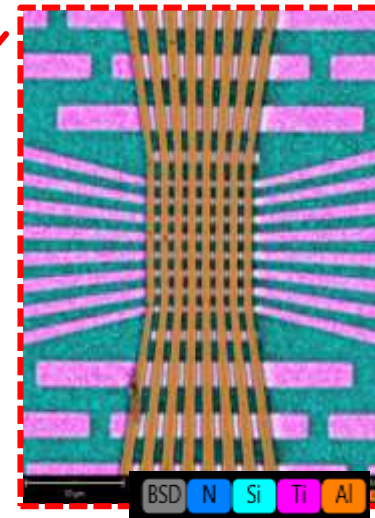
Development of a CMOS compatible fabrication process



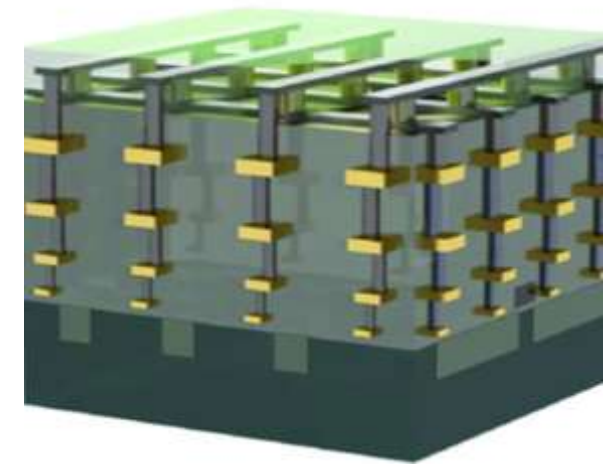
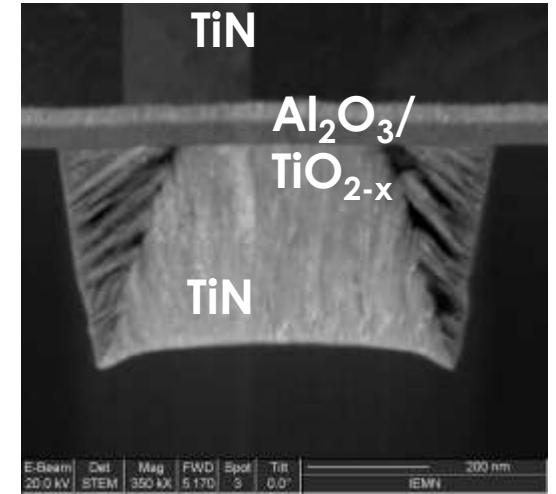
- /Metals/Al
- /Metals/Cu
- /Metals/Ti
- /Metals/TiN
- /Nitrides/Si3N4\_LPCVD
- /Nitrides/Si3N4\_PECVD
- /Organics/Polymer
- /Organics/Resist
- /Oxides/Al2O3\_ALD
- /Oxides/TiO2\_Sputtering



30 μm



10 μm

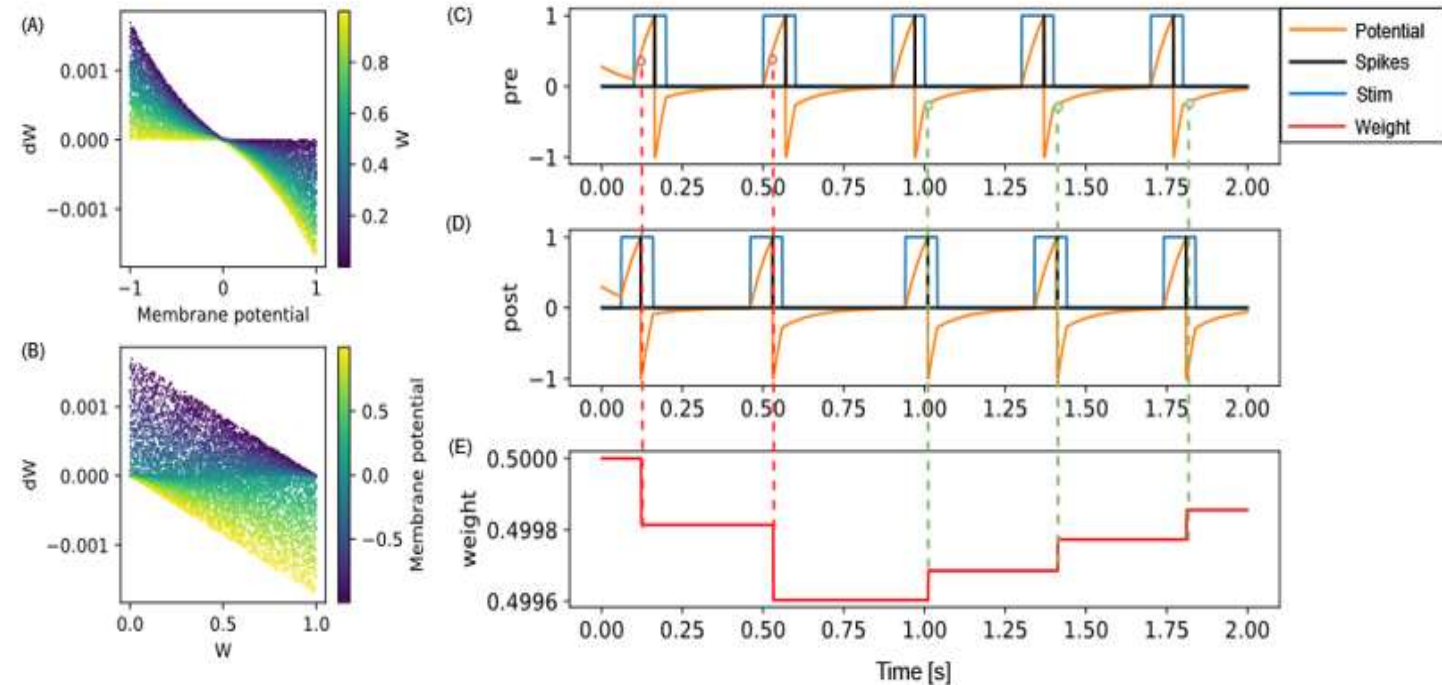
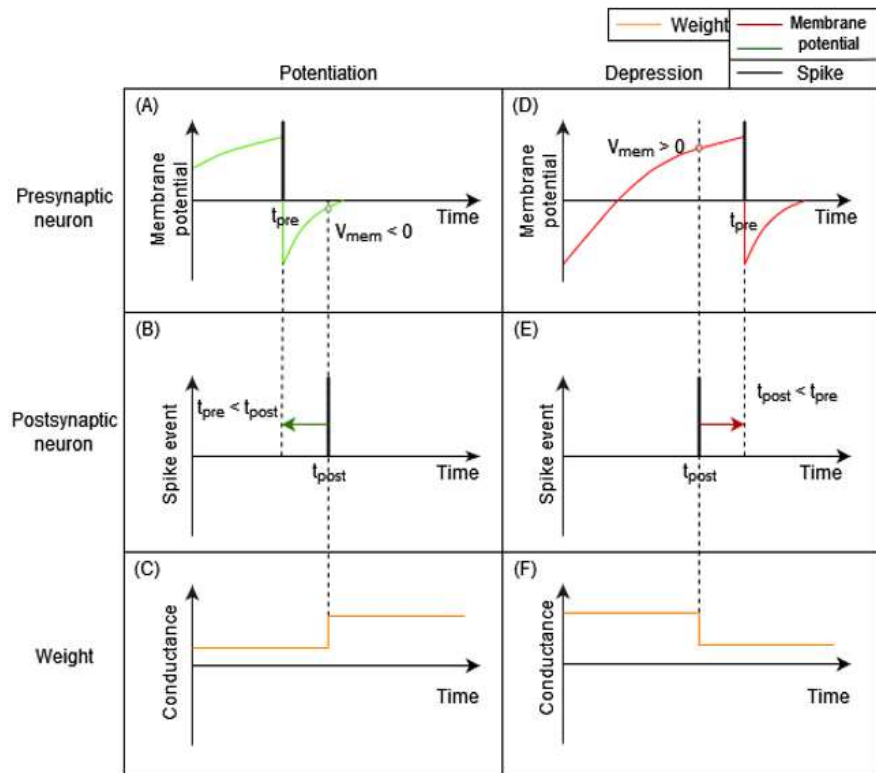




# Hardware friendly learning algorithm: VDSP (1)

19

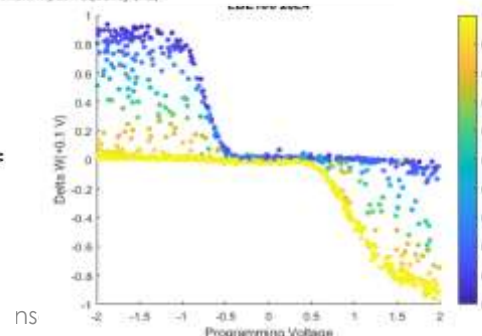
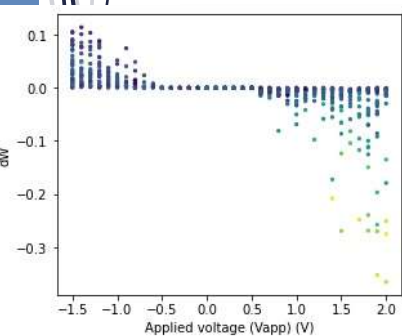
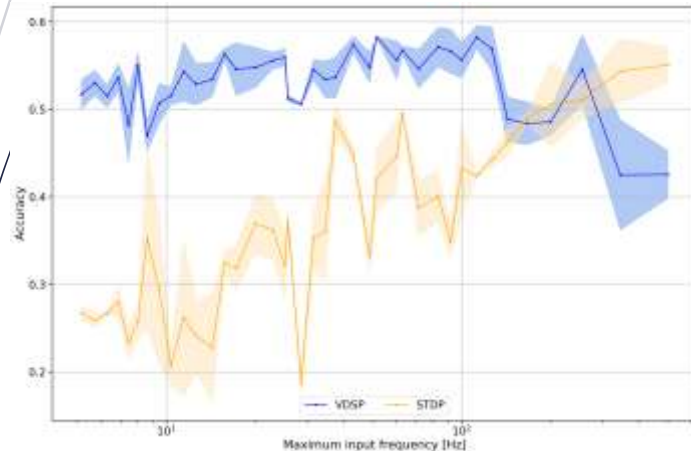
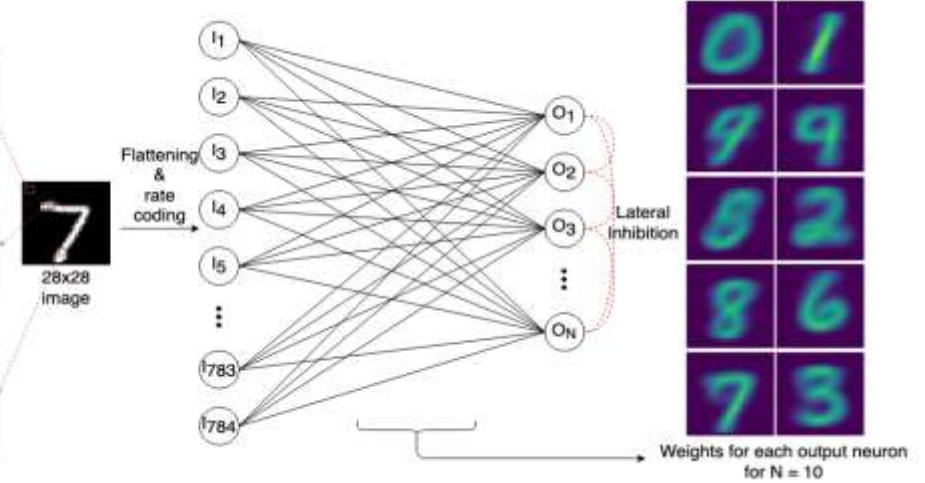
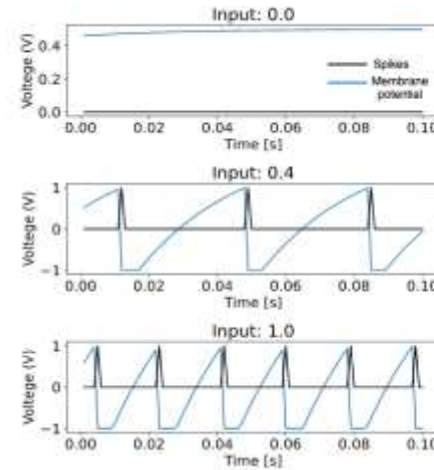
- We propose an adaptation of STDP that solves major constraints of material implementation. VDSP relies on membrane potential instead of timing and reproduce key STDP features, while material implementation is largely simplified



20

Evaluation of VDSP performances on MNIST classification:

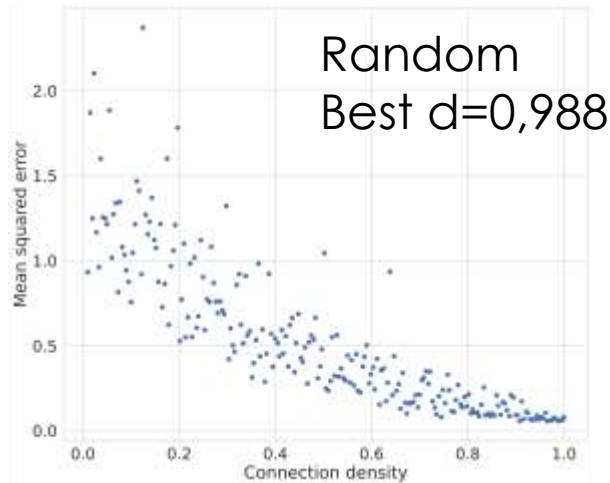
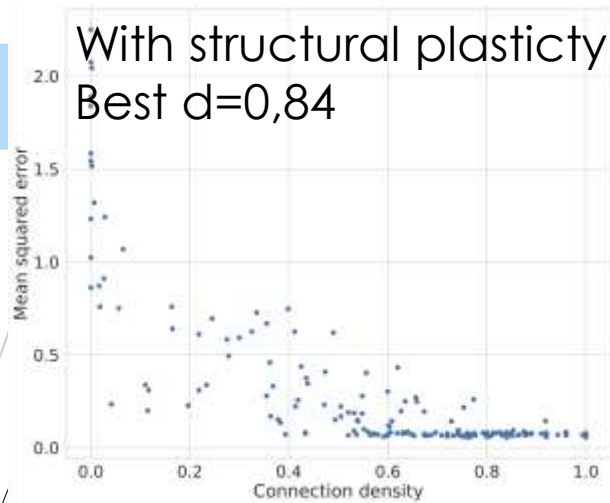
- SotA performances
- Frequency adaptation
- Compatible with Memristor variability



| This work |        |                               | Past studies |        |             |                         |
|-----------|--------|-------------------------------|--------------|--------|-------------|-------------------------|
| Neurons   | Epochs | Accuracy (%) $\mu \pm \sigma$ | Neurons      | Epochs | Accuracy(%) | Ref                     |
| 10        | 1      | 61.4 $\pm$ 0.78               | 10           | 1      | 60          | (Querlioz et al., 2013) |
| 50        | 1      | 78.84 $\pm$ 1.28              | 50           | 1      | 76.8        | (Guo et al. 2019)       |
| 50        | 3      | 81.3 $\pm$ 1.76               | 50           | 3      | 77.2        | (Boybat et al. 2018)    |
| 100       | 3      | 84.74 $\pm$ 1.08              | 50           | 3      | 81          | (Querlioz et al., 2013) |
| 100       | 5      | 85.01 $\pm$ 0.76              | 100          | 3      | 82.9        | (Diehl and Cook, 2015)  |
| 400       | 3      | 89.26 $\pm$ 0.54              | 400          | 3      | 87          | (Diehl and Cook, 2015)  |
| 400       | 5      | 89.93 $\pm$ 0.41              |              |        |             |                         |

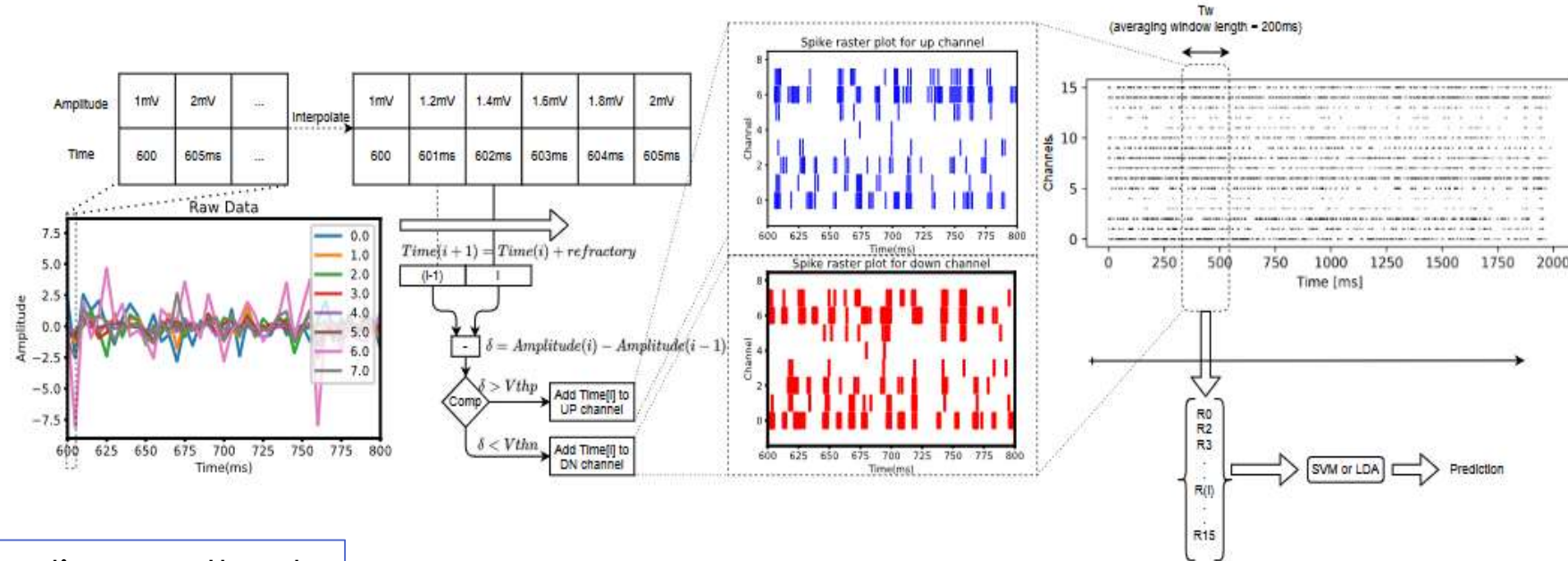
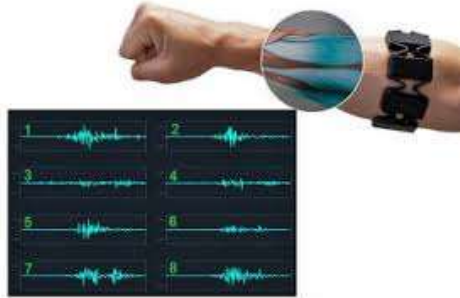
# SNN topologies: structural plasticity

21

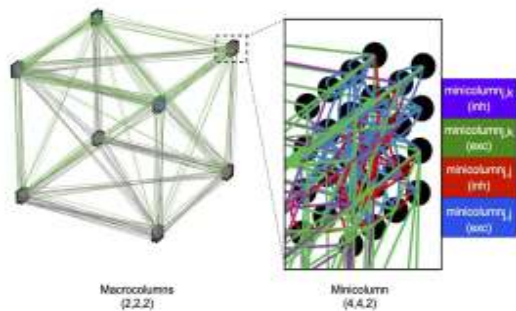


Defining the building block topologies: can we take inspiration of neuron genesis for optimal SNN definition?

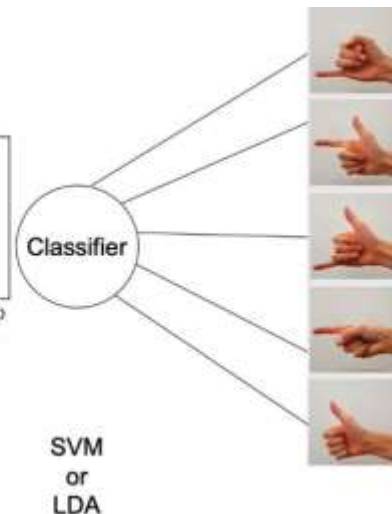
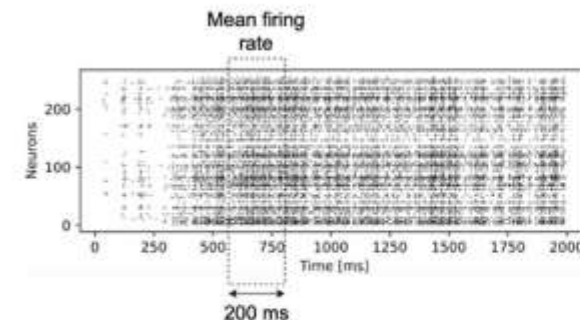
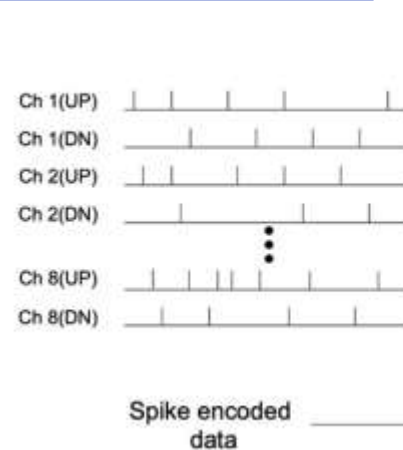




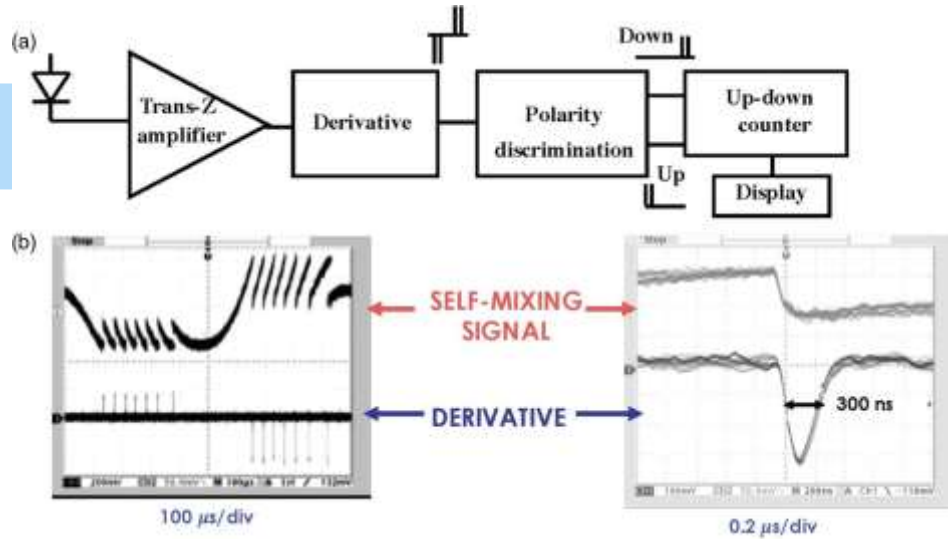
- Optimization of spike encoding methods
- SotA performances for EMG dataset
- Reservoir optimization



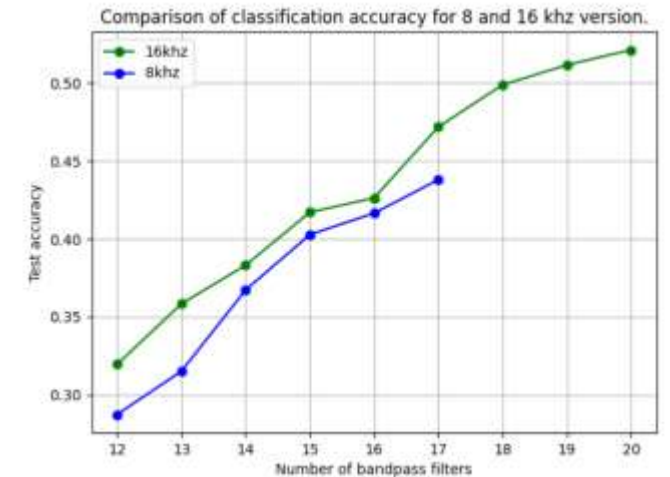
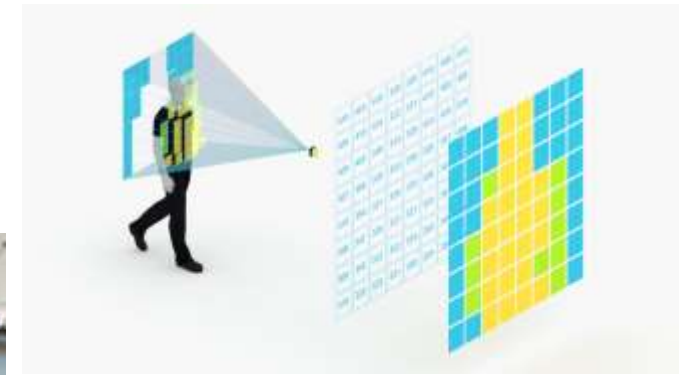
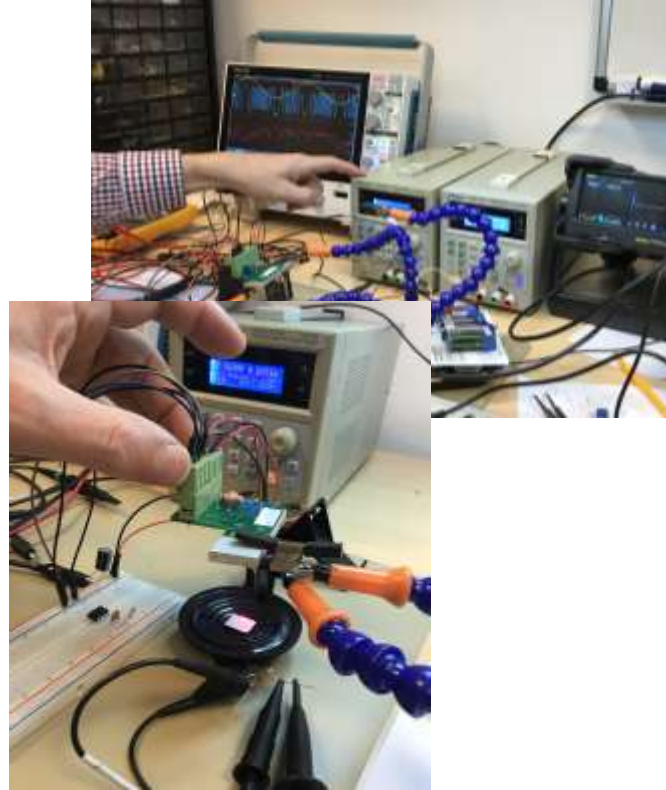
UNICO – Consortium Confidential



# SNN applications : ToF sensors



- Spike encoding in-sensor
- Circuit overhead design and optimization
- Benchmarking on audio signal (through HP membrane movement)



"Audiomnist" dataset consists of 30000 audio samples of spoken digits (0-9) of 60 different speakers

# Next steps

24

- ▶ Finalization of CMOS chip for neuron / synapses validation
- ▶ Fabrication of memristor (TiO<sub>2</sub>, HZO) in the BEOL
- ▶ Spiking ToF sensor in hardware demo
- ▶ Diversification of bio-signals (EEG, ECoG dataset under investigation) for benchmarking
- ▶ Chip 2 design for BB demonstration

# Dissemination / production

25

## Scientific production:

- HZO: Adv. Elect. Mat 2022
- TiO<sub>2</sub>: MNE 2022
- EMG: ICONS 2021
- VDSP: Frontiers (in prep 2022)

## Data sharing:

- TiO<sub>2</sub> modeling in open access through repository
- Datasets and benchmarking in open access

## Conferences:

- ICONS
- D. Querlioz, "Equilibrium Propagation: a Road for Physics-Based Learning", Keynote presentation, Third International Workshop on Theoretical and Experimental Material Computing, Helsinki, Finland, October 2021
- D. Querlioz, "Equilibrium Propagation: a Road for Physics-Based Learning", virtual 84. Annual Meeting of DPG and DPG-Tagung (DPG Meeting) of the Condensed Matter Section (SKM), September 2021.

Thank you for your attention!